

# HSM2836C

## Silicon Epitaxial Planar Diode for High Speed Switching

# HITACHI

Rev. 2  
Aug. 1995

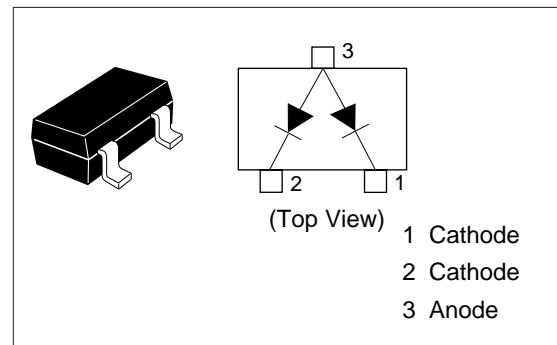
### Features

- Fast recovery time.
- MPAK package is suitable for high density surface mounting and high speed assembly.

### Ordering Information

Type No.	Laser Mark	Package Code
HSM2836C	A 4	MPAK

### Pin Arrangement



### Absolute Maximum Ratings \*\* (Ta = 25°C)

Item	Symbol	Value	Unit
Peak reverse voltage	$V_{RM}$	85	V
Reverse voltage	$V_R$	80	V
Peak forward current	$I_{FM}$	300	mA
Non-Repetitive peak forward surge current	$I_{FSM}^*$	4	A
Average forward current	$I_o$	100	mA
Junction temperature	$T_j$	125	°C
Storage temperature	$T_{stg}$	-55 to +125	°C

\* Within 1 $\mu$ s forward surge current.

\*\* Per one device

### Electrical Characteristics \* (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	$V_{F1}$	—	0.72	1.0	V	$I_F = 10$ mA
	$V_{F2}$	—	0.83	1.0		$I_F = 50$ mA
	$V_{F3}$	—	0.90	1.2		$I_F = 100$ mA
Reverse current	$I_R$	—	—	0.1	$\mu$ A	$V_R = 80$ V
Capacitance	C	—	2.5	4.0	pF	$V_R = 0$ V, $f = 1$ MHz
Reverse recovery time	$t_{rr}$	—	—	20	ns	$I_F = 10$ mA, $V_R = 6$ V, $R_L = 50\Omega$

\* Per one device

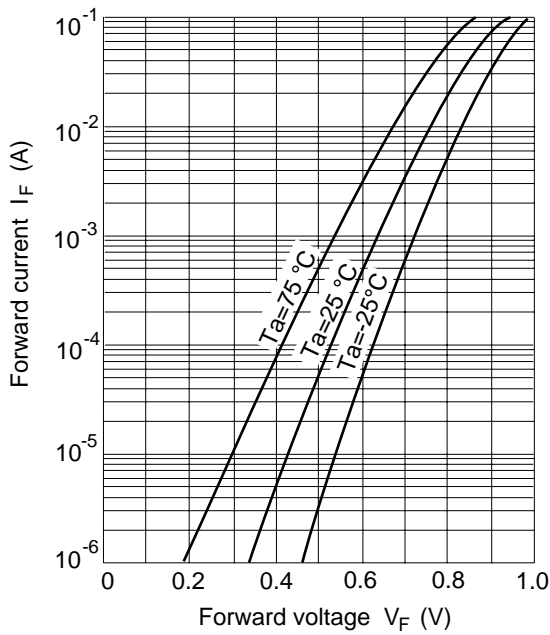


Fig.1 Forward current Vs. Forward voltage

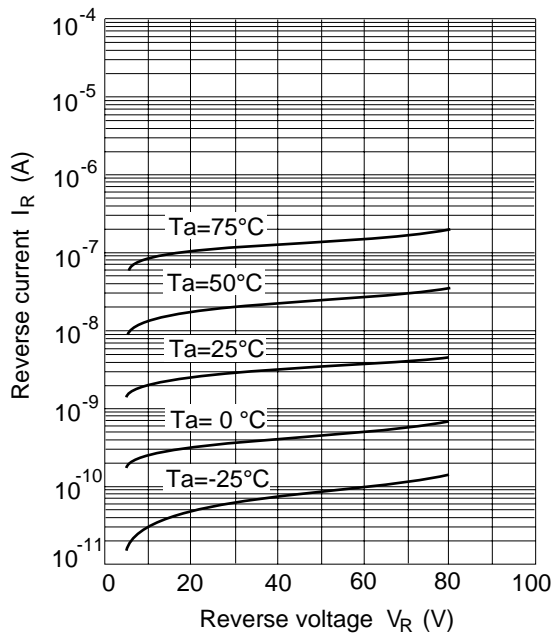


Fig.2 Reverse current Vs. Reverse voltage

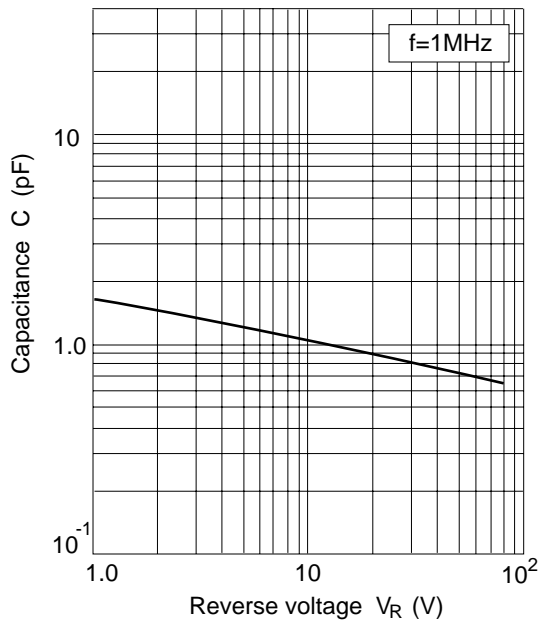


Fig.3 Capacitance Vs. Reverse voltage

Package Dimensions

Unit: mm

